

Thyristor Module

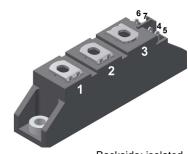
MCMA65P1600TA

V_{RRM}	<i>=</i> 2x 1600 V			
I _{tav}	=	65 A		
Vτ	=	1.17 V		

Phase leg

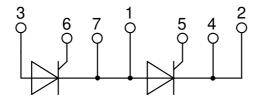
Part number

MCMA65P1600TA



Backside: isolated





Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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MCMA65P1600TA

Thyristo					Ratings		!
Symbol	Definition	Conditions		min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forward	blocking voltage	$T_{vJ} = 25^{\circ}C$			1700	1
V _{RRM/DRM}	max. repetitive reverse/forward bloc		$T_{vJ} = 25^{\circ}C$			1600	١
R/D	reverse current, drain current	V _{R/D} = 1600 V	$T_{vJ} = 25^{\circ}C$			100	μ/
		$V_{R/D} = 1600 V$ $T_{VJ} = 140^{\circ}C$		10	m/		
V _T	forward voltage drop	$I_{T} = 65 A$	$T_{VJ} = 25^{\circ}C$			1.20	١
		I _T = 130 A				1.45	١
		I _T = 65 A	T _{vJ} = 125°C			1.17	١
		I _T = 130 A				1.48	١
I _{tav}	average forward current	T _c = 85°C	T _{vJ} = 140°C			65	1
I _{T(RMS)}	RMS forward current	180° sine				105	ļ
V _{T0}	threshold voltage		T _{v.i} = 140°C			0.85	١
r _T	slope resistance } for power los	s calculation only				4.8	m۵
R _{thJC}	thermal resistance junction to case					0.5	K/W
R _{thCH}	thermal resistance case to heatsink				0.2		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		-	230	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{y_1} = 45^{\circ}C$			1.15	k/
•TSM		t = 8,3 ms; (60 Hz), sine	$V_{\rm N} = 0 V$			1.24	k/
		t = 0,0 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{VJ} = 140^{\circ}C$			980	4
		t = 8,3 ms; (60 Hz), sine	$V_{\rm NJ} = 140$ C $V_{\rm R} = 0$ V			1.06	k/
l²t	value for fusing	t = 0.3 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$				ļ
1-1	value for fusing					6.62	1
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			6.40	-
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 140 ^{\circ}\text{C}$			4.80	kA ²
_		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$		- 4	4.63	¦
CJ	junction capacitance	$V_{R} = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		54		pl
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 140 ^{\circ}C$			10	W
		t _P = 300 μs				5	W
P _{GAV}	average gate power dissipation					0.5	N
(di/dt) _{cr}	critical rate of rise of current	$T_{v_J} = 140 ^{\circ}C; f = 50 Hz$ r	repetitive, $I_T = 195 A$			150	A/μ
		t_{P} = 200 µs; di _G /dt = 0.45 A/µs;					
		$I_{G} = 0.45 \text{ A}; V = \frac{2}{3} V_{DRM}$ r	non-repet., $I_{T} = 65 A$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 140^{\circ}C$			1000	V/μ
		$R_{GK} = \infty$; method 1 (linear volta	age rise)				
V _{gt}	gate trigger voltage	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40 ^{\circ}C$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{VJ} = 25^{\circ}C$			95	m/
		2	$T_{VJ} = -40$ °C			200	m/
V _{gd}	gate non-trigger voltage	$V_{\rm D} = \frac{2}{3} V_{\rm DBM}$	$T_{VJ} = 140^{\circ}C$			0.2	
I _{GD}	gate non-trigger current		V3			10	i.
	latching current	t _p = 10 μs	$T_{VJ} = 25 ^{\circ}C$			200	m/
•L		$l_{g} = 0.45 \text{ A}; \text{ di}_{g}/\text{dt} = 0.45 \text{ A}/\mu$				200	
	holding ourrant	$V_{\rm D} = 6 V R_{\rm GK} = \infty$	$T_{\rm VJ} = 25^{\circ}\rm C$			200	m
I _H	holding current						m/
t _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25 ^{\circ}C$			2	μ
	to an all the a	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu$			4-4		
t _q	turn-off time	$V_{R} = 100 \text{ V}; I_{T} = 65\text{A}; \text{V} = 100 \text{ V};$			150		μ
		$di/dt = 10 \text{ A}/\mu \text{s} dv/dt = 20 \text{ V}$	V/μs_t _p = 200 μs				

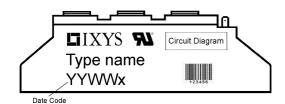
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20191209d



MCMA65P1600TA

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					120	Α
T _{vj}	virtual junction temperature				-40		140	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque		2.5		4	Nm		
d _{Spp/App}	creepage distance on surface striking distance thro		terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage ustance on surract		terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			4800			V
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA		4000			V



Part description

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA65P1600TA	MCMA65P1600TA	Box	36	512930

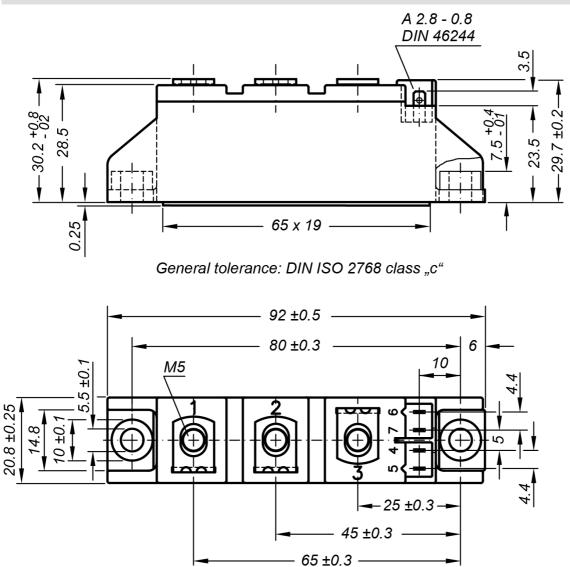
Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140^{\circ}C$
)[R]-	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	3.6		mΩ

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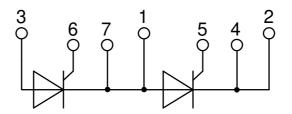


Outlines TO-240AA



Optional accessories for modules

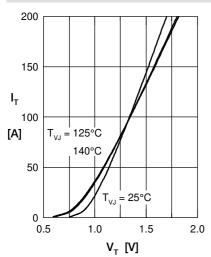
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red Type ZY 200L (L = Left for pin pair 4/5) Type ZY 200R (R = Right for pin pair 6/7) UL 758, style 3751



MCMA65P1600TA



Thyristor



1200

 I_{TSM}^{800}

400

100.0

10.0

1.0

0.1

0.01

0.10

t_{gd}

0.01

[A]

50 Hz, 80% V

40'

0.1

t [s]

 \mathbf{I}_{TSM} : crest value, t: duration

T_{VJ} = 25°C

1.00

I_G [A]

Fig. 5 Gate controlled delay time t_{ad}

lim

10.00

Fig. 2 Surge overload current

45°C V.I

Fig. 1 Forward characteristics

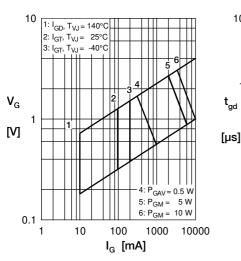


Fig. 4 Gate voltage & gate current

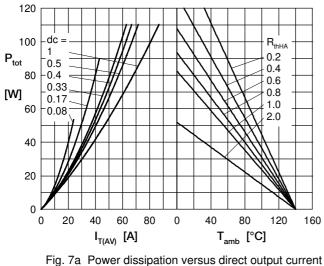
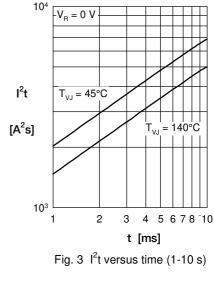
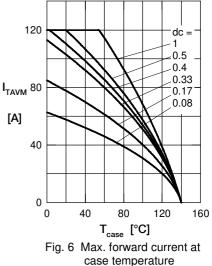


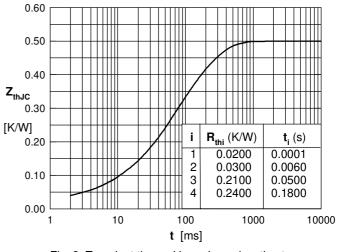
Fig. 7b and ambient temperature



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